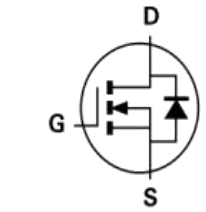
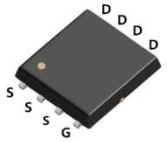
60V N-Channel Enhancement Mode MOSFET

MAIN CHARACTERISTICS

I_D	160A
V_{DSS}	60V
R_{DSON}-typ(@V_{GS}=10V)	<3mΩ(Type:2.8mΩ)





PDFN5*6-8L

Features

Adopt advanced trench technology to provide excellent Battery protection or in other Switching application.

Applications

- Battery protection
- Load switch
- Uninterruptible power supply
- YFW-SGT technology

Mechanical Data

- Case: Molded plastic
- Mounting Position: Any
- Molded Plastic: UL Flammability Classification Rating 94V-0
- Lead free in compliance with EU RoHS 2011/65/EU directive
- Solder bath temperature 275℃ maximum,10s per JESD 22-B106

Product Specification Classification

Part Number	Package	Marking	Pack
YFWG160N06NF	PDFN5*6-8L	YFW G160N06NF XXXXX	5000PCS/Tape

Maximum Ratings at Tc=25°C unless otherwise specified

Characteristics	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	60	V
Gate-Source Voltage	V_{GS}	±20	V
Continue Drain Current	I_D	160	A
Pulsed Drain Current (Note1)	I_{DM}	240	A
Power Dissipation	P_D	210	W
Single Pulse Avalanche Energy (Note1)	E_{AS}	650	mJ
Operating Temperature Range	T_J	150	°C
Storage Temperature Range	T_{STG}	-55 to +150	°C
Thermal Resistance, Junction to Case	$R_{\theta JC}$	0.59	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	50	°C/W

Note1:Pulse test: 300 μs pulse width, 2 % duty cycle

Electrical Characteristics at Tc=25°C unless otherwise specified

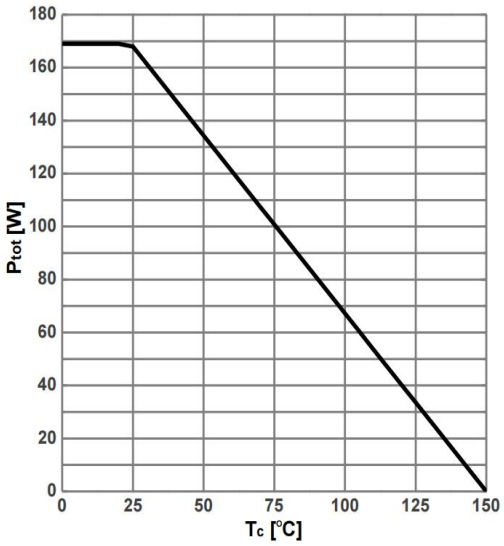
Characteristics	Test Condition	Symbol	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	V_{GS} = 0 V,I_D = 250 μA	BV_{DSS}	60	-	-	V
Drain-Source Leakage Current	V_{DS} = 60 V, V_{GS} = 0 V	I_{DSS}	-	-	1	μA
Gate Leakage Current	V_{GS} = ± 20 V, V_{DS} = 0 V	I_{GSS}	-	-	±100	nA
Gate-Source Threshold Voltage	V_{DS} = V_{GS} , I_D = 250 μA	$V_{GS(th)}$	2	-	4	V
Drain-Source On-State Resistance	V_{GS} = 10 V, I_D = 20A	$R_{DS(on)}$	-	2.8	3	mΩ
Transconductance	V_{DS}=5V, I_D=20A	gfs		130		S
Input Capacitance	V_{DS}=25V , V_{GS}=0V , f=1MHz	C_{iss}	-	4200	-	pF
Output Capacitance		C_{oss}	-	1080	-	pF
Reverse Transfer Capacitance		C_{rss}	-	41	-	pF
Turn-on Delay Time(Note2)	V_{DD}=30V , V_{GS}=10V , RG=3Ω , I_D=100 A	$t_{d(ON)}$	-	13.5	-	ns
Rise Time(Note2)		t_r	-	95.5	-	ns
Turn-Off Delay Time(Note2)		$t_{d(OFF)}$	-	40	-	ns
Fall Time(Note2)		t_f	-	110	-	ns
Total Gate Charge(Note2)	V_{DS}=30V , V_{GS}=10V , I_D=20A	Q_G	-	42	-	nC
Gate to Source Charge(Note2)		Q_{GS}	-	10	-	nC
Gate to Drain Charge(Note2)		Q_{GD}	-	12	-	nC

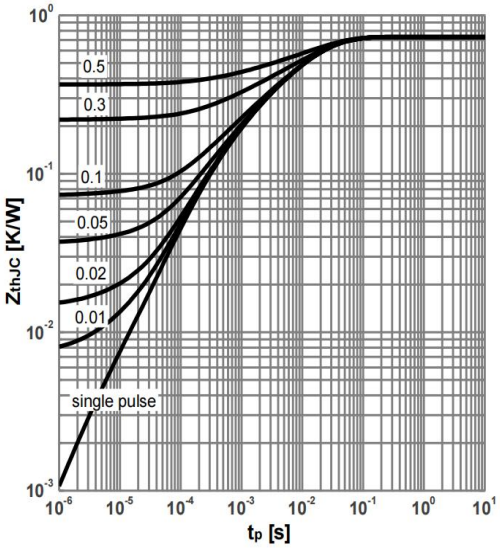
Source-Drain Diode Characteristics at Ta=25°C unless otherwise specified

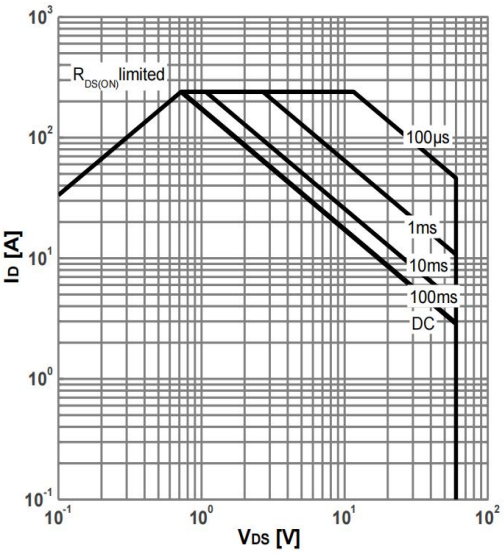
Characteristics	Test Condition	Symbol	Min.	Typ.	Max.	Unit
Maximun Body-Diode Continuous Current		I_S	-	-	160	A
Drain-Source Diode Forward Voltage	V_{GS}=0V , I_S=20A , T_J=25℃	V_{SD}	-	-	1.2	V
Reverse Recovery Time(Note2)	T_J = 25℃, I_F=60A di / dt = 100 A/μs	trr	-	35	-	ns
Reverse Recovery Charge(Note2)		Qrr	-	30	-	nC

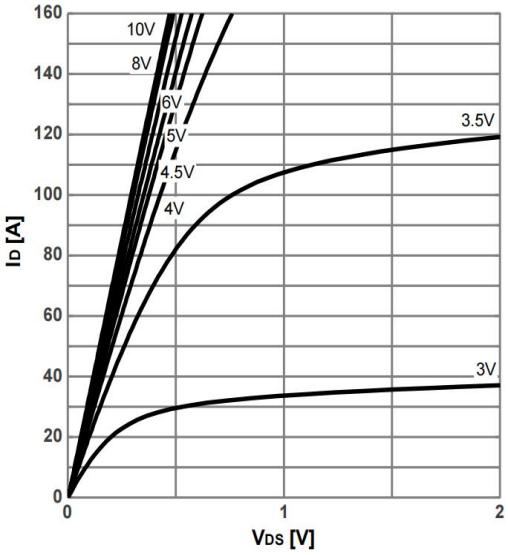
Note2:Pulse test: 300 μs pulse width, 2 % duty cycle

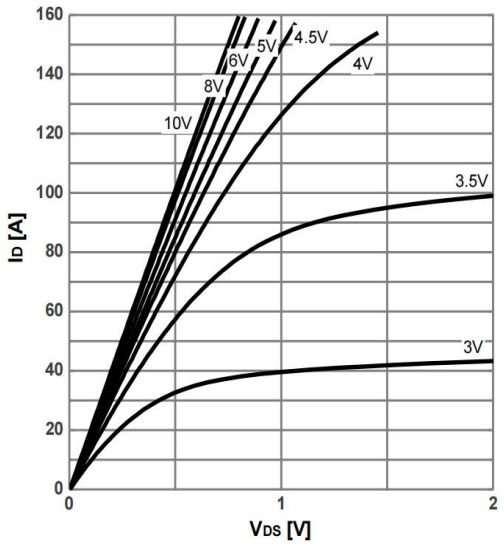
RATINGS AND CHARACTERISTIC CURVES

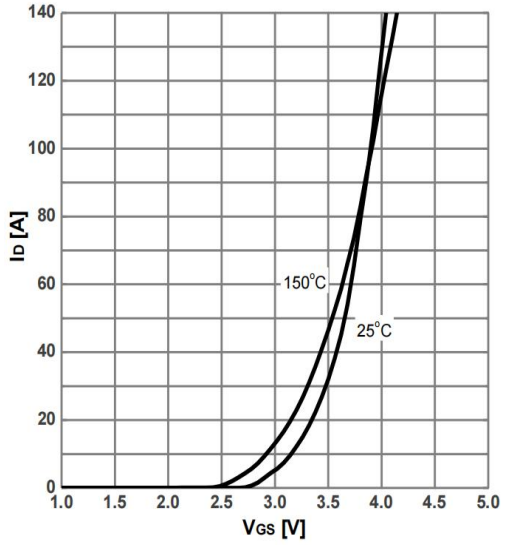












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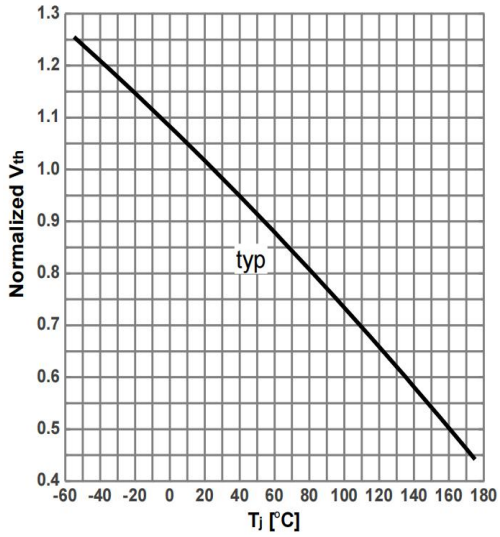

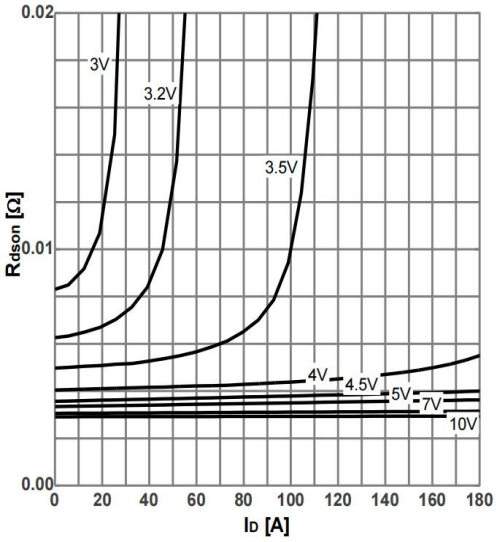

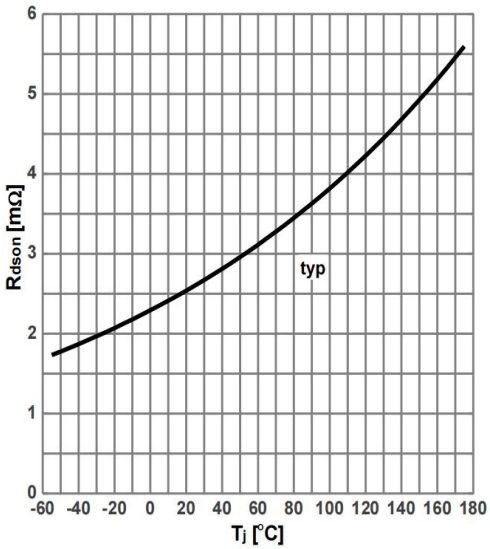

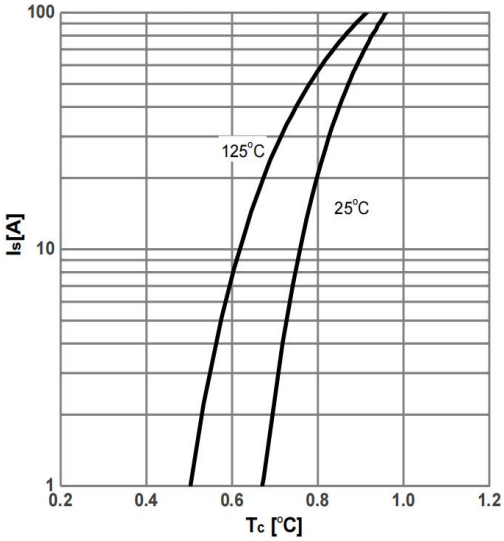

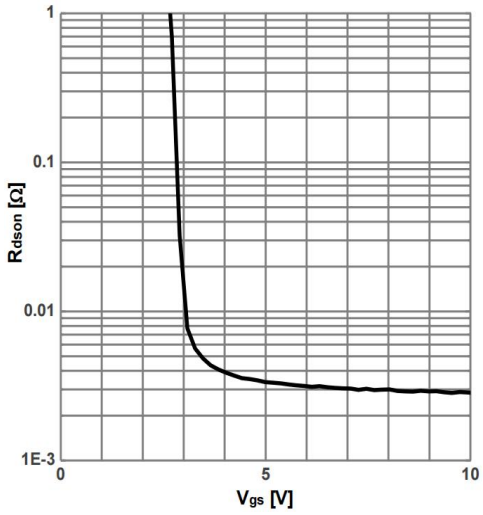

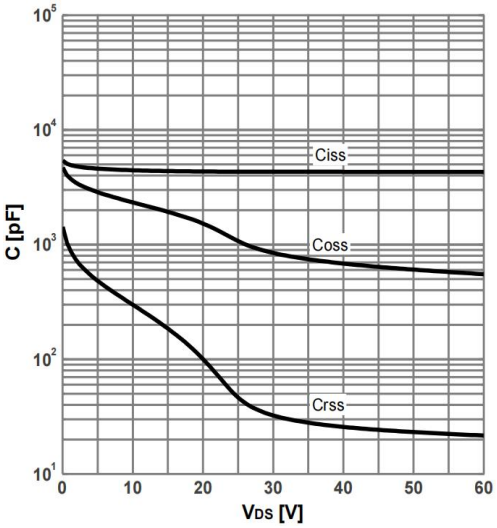

Package Outline Dimensions Millimeters

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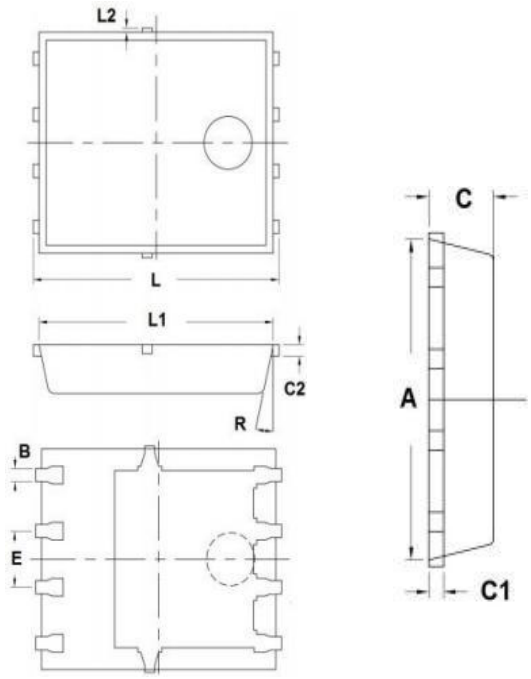

Dim.	Min.	Max.
A	4.8	5.2
B	0.25	0.35
C	1	1.2
C1	Typ0.254	
C2	Typ0.254	
E	Typ1.27	
L	6	6.3
L1	5.7	6
L2	Max0.2	
R	Typ13°	
All Dimensions in millimeter		